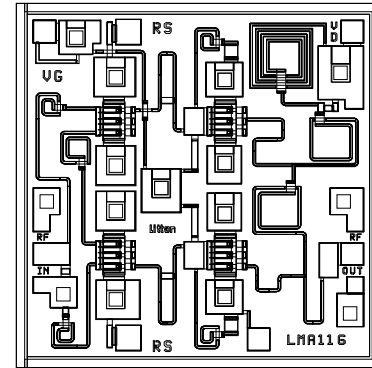


**Features**

- 4.5dB Typical Noise Figure
- 15dB Typical Gain
- 18dBm Saturated Output Power
- 12dB Input/Output Return Loss Typical
- 2-10GHz Frequency Bandwidth
- +8 Volts Single Bias Supply
- DC Decoupled RF Output
- Chip Size : 1.62mmX1.62mm (.064"X.064")
- Chip Thickness : 100µm
- Pad Dimension : 100µm<sup>2</sup>



**Description**

The Filtronic LMA116 is a GaAs monolithic distributive amplifier which operates from 2 to 10GHz. This amplifier is self biased and four 450µm FETs are used to produce a typical gain of 15dB and a noise figure of 4.5dB. The LMA116 is suitable for gain block, low noise and driver amplifier applications. DC decoupled output RF port. Ground is provided to the circuitry through vias to the backside metallization.

**Electrical Specifications at T<sub>a</sub>=25°C**

(V<sub>DD</sub>=+8.0V, Z<sub>in</sub>=Z<sub>out</sub>=50Ω)

Symbol	Parameter	Test Conditions	Limit			Units
			Min.	Typ.	Max.	
BW	Operating Bandwidth		2		10	GHz
S21	Small Signal Gain	VD=8V, VG=3.5V, Rs1=5Ω	13	15		dB
I <sub>ds</sub>	Drain Operating Current		55	80	125	mA
ΔS21	Small Signal Gain Flatness			±1	±1.5	dB
NF	Noise Figure	@ .5Idss		4.5	5.5	dB
RL <sub>in</sub>	Input Return Loss			-10		dB
RL <sub>out</sub>	Output Return Loss			-14		dB
S12	Reverse Isolation		-35	-40		dB
P-1dB	1-dB Gain Compression Power		12.5	15		dBm

**Absolute Maximum Ratings**

Symbol	Parameter/Conditions	Min.	Max.	Units
V <sub>dd</sub>	Drain Supply Voltage		12	Volts
I <sub>dd</sub>	Total Drain Current		125	mA
P <sub>in</sub>	RF Input Power		24	dBm
P <sub>t</sub>	Power Dissipation		1.5	W
T <sub>ch</sub>	Operating Channel Temperature		150	°C
T <sub>stg</sub>	Storage Temperature	-65	165	°C
T <sub>max.</sub>	Max. Assembly Temp. (1 min. max.)		300	°C

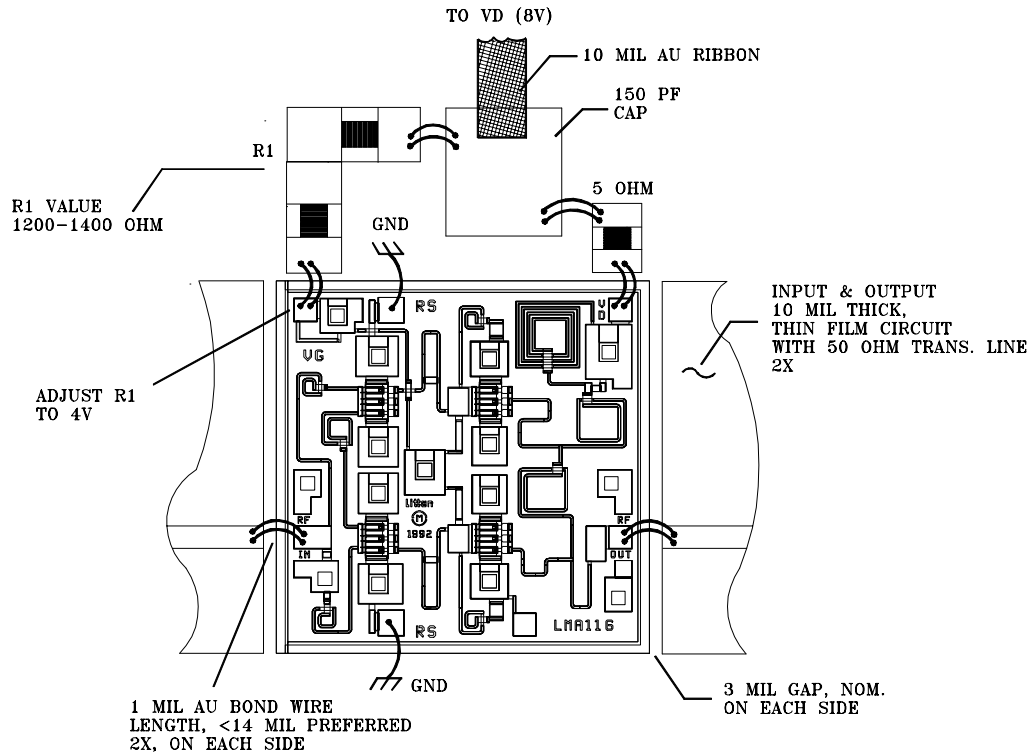
**Notes :**

1. This GaAs MMIC is susceptible to damage from Electrostatic Discharge. Proper precautions should be used when handling these devices.
2. Specifications subject to change without notice.
3. On-chip 5Ω resistor set I<sub>ds</sub> of 80mA typical.

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**Assembly Diagram**

**SINGLE VOLTAGE SUPPLY SCHEME**



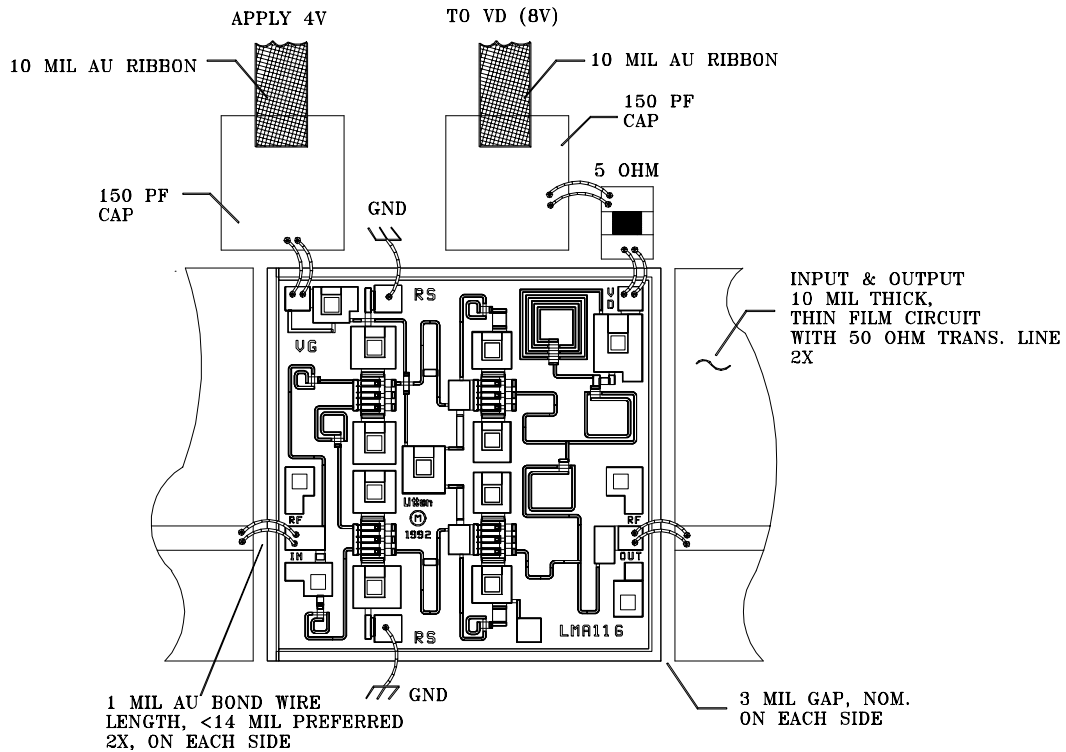
**Notes:**

- 1.) Recommended lead bond technique is thermocompression wedge bonding with 0.001" (25µm) diameter wire. The bond tool force shall be 35-38 gram. Bonding stage temperature shall be 230-240°C, heated tool (150-160°C) is recommended. Ultrasonic bonding is not recommended.
- 2.) The recommended die attach is Ablebond silver epoxy, the stabilize bake temperature is set at 150°C for 45 minutes.
- 3.) Bond on bond or stitch bond acceptable.
- 4.) Conductor over conductor acceptable. Conductors must not short.

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**Assembly Diagram**

**TWO VOLTAGE SUPPLY SCHEME**

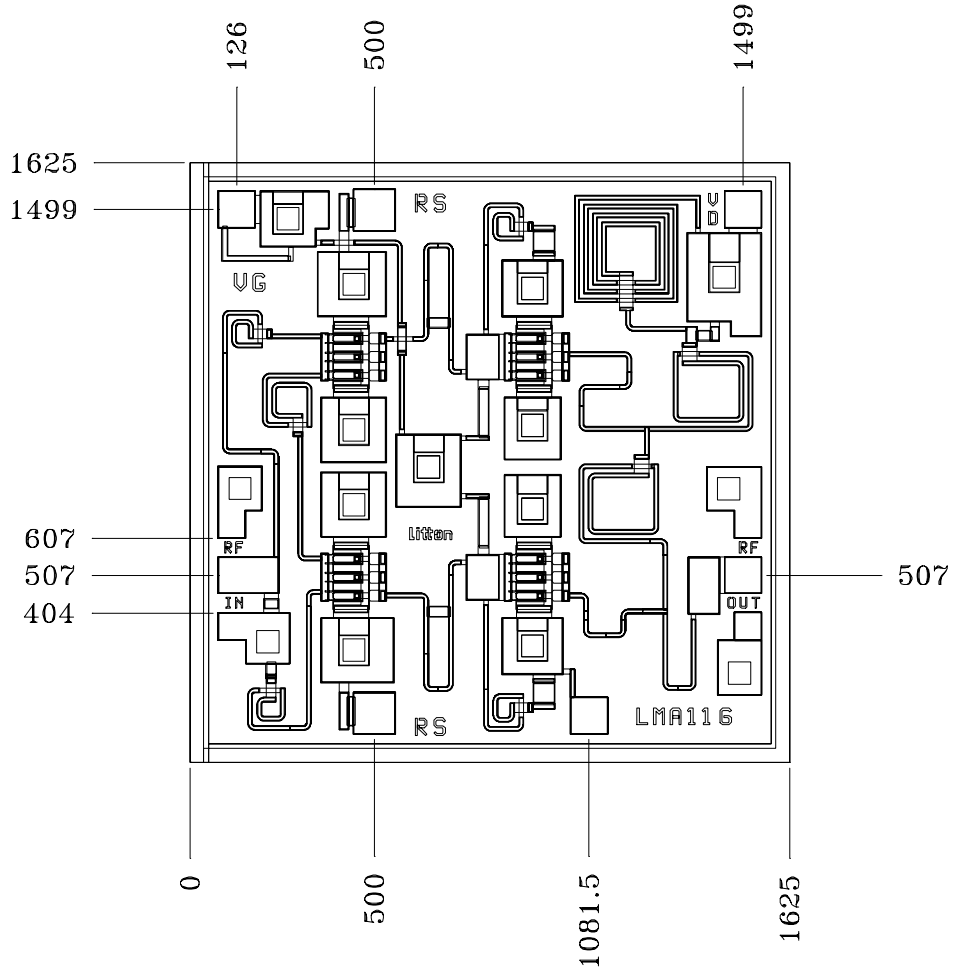


**Notes:**

- 1.) Recommended lead bond technique is thermocompression wedge bonding with 0.001" (25µm) diameter wire. The bond tool force shall be 35-38 gram. Bonding stage temperature shall be 230-240°C, heated tool (150-160°C) is recommended. Ultrasonic bonding is not recommended.
- 2.) The recommended die attach is Ablebond silver epoxy, the stabilize bake temperature is set at 150°C for 45 minutes.
- 3.) Bond on bond or stitch bond acceptable.
- 4.) Conductor over conductor acceptable. Conductors must not short.

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**Mechanical Outline**



**Notes:**

- 1.) Unless Otherwise specified.
- 2.) All units are in micron ( $\mu\text{m}$ ).
- 3.) All bond pads are 100 X 100  $\mu\text{m}^2$ .
- 4.) Bias pad ( $V_{DD}$ ) size is 100 X 121.5  $\mu\text{m}^2$ .

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